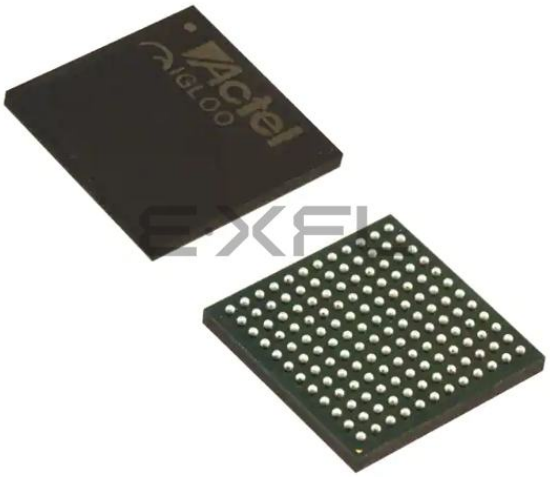

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	24576
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl1000v5-fg144

Combinatorial Cells Contribution—$P_{C\text{-}CELL}$

$P_{C\text{-}CELL} = N_{C\text{-}CELL} * \alpha_1 / 2 * P_{AC7} * F_{CLK}$

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

Routing Net Contribution—P_{NET}

$P_{NET} = (N_{S\text{-}CELL} + N_{C\text{-}CELL}) * \alpha_1 / 2 * P_{AC8} * F_{CLK}$

$N_{S\text{-}CELL}$ is the number of VersaTiles used as sequential modules in the design.

$N_{C\text{-}CELL}$ is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution—P_{INPUTS}

$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * P_{AC9} * F_{CLK}$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

I/O Output Buffer Contribution—$P_{OUTPUTS}$

$P_{OUTPUTS} = N_{OUTPUTS} * \alpha_2 / 2 * \beta_1 * P_{AC10} * F_{CLK}$

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in Table 2-23 on page 2-19.

β_1 is the I/O buffer enable rate—guidelines are provided in Table 2-24 on page 2-19.

F_{CLK} is the global clock signal frequency.

RAM Contribution—P_{MEMORY}

$P_{MEMORY} = P_{AC11} * N_{BLOCKS} * F_{READ\text{-}CLOCK} * \beta_2 + P_{AC12} * N_{BLOCK} * F_{WRITE\text{-}CLOCK} * \beta_3$

N_{BLOCKS} is the number of RAM blocks used in the design.

$F_{READ\text{-}CLOCK}$ is the memory read clock frequency.

β_2 is the RAM enable rate for read operations.

$F_{WRITE\text{-}CLOCK}$ is the memory write clock frequency.

β_3 is the RAM enable rate for write operations—guidelines are provided in Table 2-24 on page 2-19.

PLL Contribution—P_{PLL}

$P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$

F_{CLKOUT} is the output clock frequency.†

† *If a PLL is used to generate more than one output clock, include each output clock in the formula by adding its corresponding contribution ($P_{AC13} * F_{CLKOUT}$ product) to the total PLL contribution.*

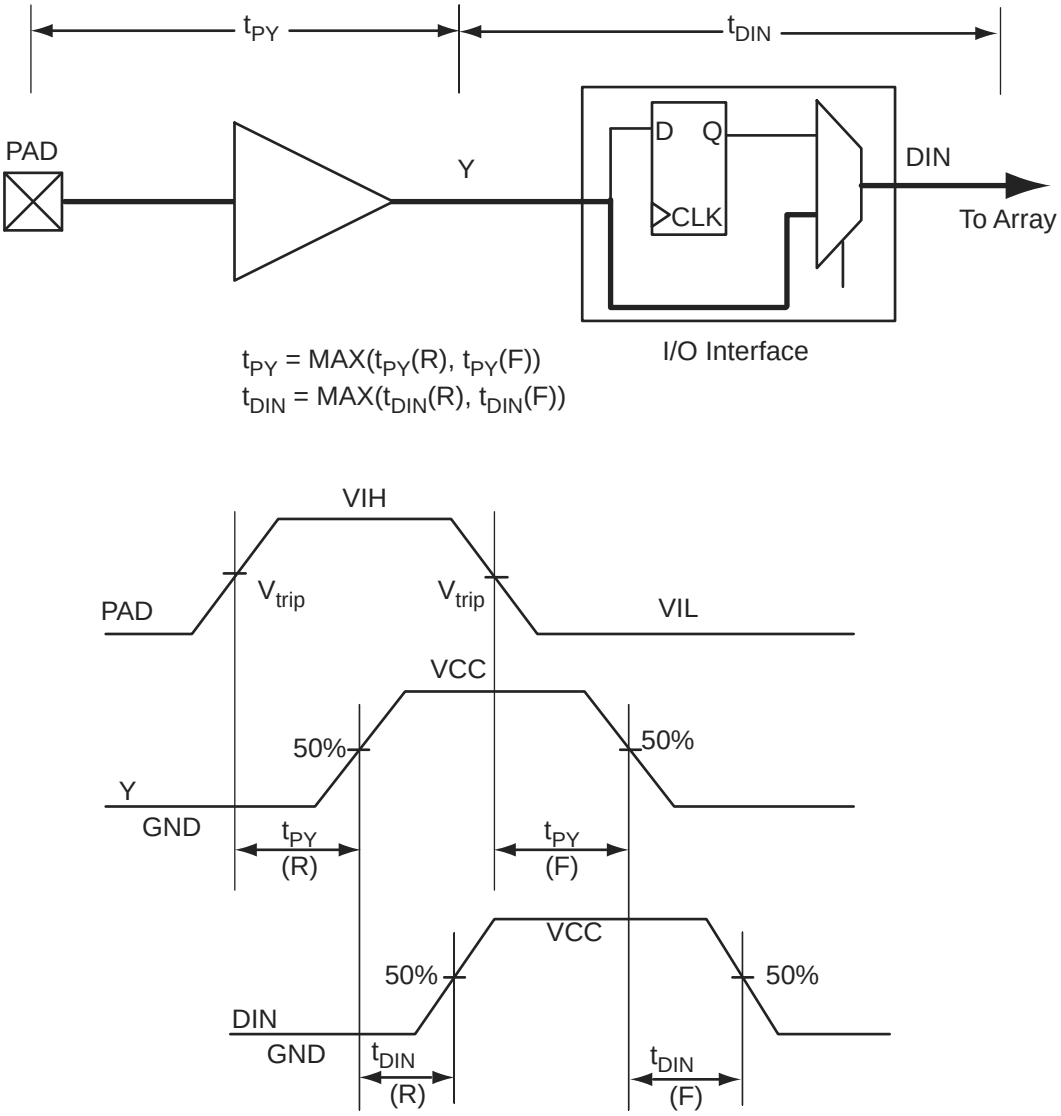


Figure 2-4 • **Input Buffer Timing Model and Delays (example)**

Table 2-27 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		V_{IH}		VOL	V_{OH}	I_{OL}[1]	I_{OH}[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-36 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case V_{CC} = 1.14 V, Worst-Case VCCI (per standard) Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
3.3 V LVCMOS Wide Range[3]	100 µA	8	High	5	–	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
2.5 V LVCMOS	8 mA	8	High	5	–	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns
1.8 V LVCMOS	4 mA	4	High	5	–	1.55	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	ns
1.5 V LVCMOS	2 mA	2	High	5	–	1.55	2.92	0.26	1.22	1.10	2.96	2.60	2.40	2.56	ns
1.2 V LVCMOS	1 mA	1	High	5	–	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns
1.2 V LVCMOS Wide Range[3]	100 µA	1	High	5	–	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-42 • I/O Short Currents IOSH/IOSL
Applicable to Advanced I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

*Note: *T_J = 100°C*

Table 2-54 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.90	1.98	2.13	5.96	5.49	ns
4 mA	Std.	0.97	2.32	0.18	0.85	0.66	2.37	1.90	1.98	2.13	5.96	5.49	ns
6 mA	Std.	0.97	1.94	0.18	0.85	0.66	1.99	1.57	2.20	2.53	5.58	5.16	ns
8 mA	Std.	0.97	1.94	0.18	0.85	0.66	1.99	1.57	2.20	2.53	5.58	5.16	ns
12 mA	Std.	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns
16 mA	Std.	0.97	1.75	0.18	0.85	0.66	1.79	1.40	2.36	2.79	5.38	4.99	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-55 • **3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	3.80	0.18	0.83	0.66	3.88	3.41	1.74	1.78	ns
4 mA	Std.	0.97	3.80	0.18	0.83	0.66	3.88	3.41	1.74	1.78	ns
6 mA	Std.	0.97	3.15	0.18	0.83	0.66	3.21	2.94	1.96	2.17	ns
8 mA	Std.	0.97	3.15	0.18	0.83	0.66	3.21	2.94	1.96	2.17	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-56 • **3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.19	0.18	0.83	0.66	2.24	1.79	1.74	1.87	ns
4 mA	Std.	0.97	2.19	0.18	0.83	0.66	2.24	1.79	1.74	1.87	ns
6 mA	Std.	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns
8 mA	Std.	0.97	1.85	0.18	0.83	0.66	1.89	1.46	1.96	2.26	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Applies to 1.2 V DC Core Voltage

Table 2-73 • **3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	1.55	7.52	0.26	1.32	1.10	7.52	6.38	3.84	4.02	13.31	12.16	ns
100 µA	4 mA	Std.	1.55	7.52	0.26	1.32	1.10	7.52	6.38	3.84	4.02	13.31	12.16	ns
100 µA	6 mA	Std.	1.55	6.37	0.26	1.32	1.10	6.37	5.57	4.23	4.73	12.16	11.35	ns
100 µA	8 mA	Std.	1.55	6.37	0.26	1.32	1.10	6.37	5.57	4.23	4.73	12.16	11.35	ns
100 µA	12 mA	Std.	1.55	5.55	0.26	1.32	1.10	5.55	4.96	4.50	5.18	11.34	10.75	ns
100 µA	16 mA	Std.	1.55	5.32	0.26	1.32	1.10	5.32	4.82	4.56	5.29	11.10	10.61	ns
100 µA	24 mA	Std.	1.55	5.19	0.26	1.32	1.10	5.19	4.85	4.63	5.74	10.98	10.63	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-74 • **3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	1.55	4.75	0.26	1.32	1.10	4.75	3.77	3.84	4.27	10.54	9.56	ns
100 µA	4 mA	Std.	1.55	4.75	0.26	1.32	1.10	4.75	3.77	3.84	4.27	10.54	9.56	ns
100 µA	6 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.19	4.24	4.98	9.88	8.98	ns
100 µA	8 mA	Std.	1.55	4.10	0.26	1.32	1.10	4.10	3.19	4.24	4.98	9.88	8.98	ns
100 µA	12 mA	Std.	1.55	3.73	0.26	1.32	1.10	3.73	2.91	4.51	5.43	9.52	8.69	ns
100 µA	16 mA	Std.	1.55	3.67	0.26	1.32	1.10	3.67	2.85	4.57	5.55	9.46	8.64	ns
100 µA	24 mA	Std.	1.55	3.70	0.26	1.32	1.10	3.70	2.79	4.65	6.01	9.49	8.58	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

Table 2-77 • **3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case V_{CC} = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	4 mA	Std.	1.55	6.44	0.26	1.29	1.10	6.44	5.64	2.99	3.28	ns
100 µA	6 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns
100 µA	8 mA	Std.	1.55	5.41	0.26	1.29	1.10	5.41	4.91	3.35	3.89	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-78 • **3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.7
Applicable to Standard Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	2 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	4 mA	Std.	1.55	3.89	0.26	1.29	1.10	3.89	3.13	2.99	3.45	ns
100 µA	6 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
100 µA	8 mA	Std.	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
3. *Software default selection highlighted in gray.*

Applies to 1.2 V Core Voltage

Table 2-89 • **2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
4 mA	Std.	1.55	5.59	0.26	1.20	1.10	5.68	5.14	2.82	2.80	11.47	10.93	ns
6 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
8 mA	Std.	1.55	4.76	0.26	1.20	1.10	4.84	4.47	3.10	3.33	10.62	10.26	ns
12 mA	Std.	1.55	4.17	0.26	1.20	1.10	4.23	3.99	3.30	3.67	10.02	9.77	ns
16 mA	Std.	1.55	3.98	0.26	1.20	1.10	4.04	3.88	3.34	3.76	9.83	9.66	ns
24 mA	Std.	1.55	3.90	0.26	1.20	1.10	3.96	3.90	3.40	4.09	9.75	9.68	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-90 • **2.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
4 mA	Std.	1.55	3.33	0.26	1.20	1.10	3.38	3.09	2.82	2.91	9.17	8.88	ns
6 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
8 mA	Std.	1.55	2.89	0.26	1.20	1.10	2.93	2.56	3.10	3.45	8.72	8.34	ns
12 mA	Std.	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
16 mA	Std.	1.55	2.59	0.26	1.20	1.10	2.63	2.24	3.34	3.88	8.41	8.03	ns
24 mA	Std.	1.55	2.60	0.26	1.20	1.10	2.64	2.18	3.40	4.22	8.42	7.97	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-91 • **2.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
4 mA	Std.	1.55	5.02	0.26	1.19	1.10	5.11	4.60	2.50	2.62	10.89	10.38	ns
6 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
8 mA	Std.	1.55	4.21	0.26	1.19	1.10	4.27	4.00	2.76	3.10	10.06	9.79	ns
12 mA	Std.	1.55	3.66	0.26	1.19	1.10	3.71	3.55	2.94	3.41	9.50	9.34	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-183 • **AGL060 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	2.04	2.33	ns
t_{RCKH}	Input High Delay for Global Clock	2.10	2.51	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.40	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-184 • **AGL125 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	2.08	2.54	ns
t_{RCKH}	Input High Delay for Global Clock	2.15	2.77	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Embedded FlashROM Characteristics

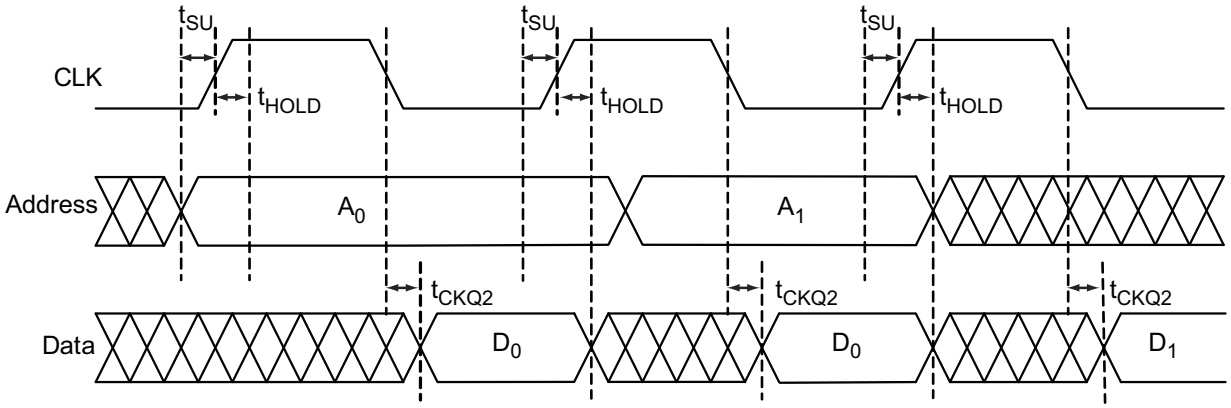


Figure 2-45 • **Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-197 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.57	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	34.14	ns
F_{MAX}	Maximum Clock Frequency	15	MHz

1.2 V DC Core Voltage

Table 2-198 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.59	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	52.90	ns
F_{MAX}	Maximum Clock Frequency	10	MHz

3 – Pin Descriptions

Supply Pins

GND **Ground**

Ground supply voltage to the core, I/O outputs, and I/O logic.

GNDQ **Ground (quiet)**

Quiet ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ must always be connected to GND on the board.

VCC **Core Supply Voltage**

Supply voltage to the FPGA core, nominally 1.5 V for IGLOO V5 devices, and 1.2 V or 1.5 V for IGLOO V2 devices. VCC is required for powering the JTAG state machine in addition to VJTAG. Even when a device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the device.

For IGLOO V2 devices, VCC can be switched dynamically from 1.2 V to 1.5 V or vice versa. This allows in-system programming (ISP) when VCC is at 1.5 V and the benefit of low power operation when VCC is at 1.2 V.

VCCIBx **I/O Supply Voltage**

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are up to eight I/O banks on IGLOO devices plus a dedicated VJTAG bank. Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VMVx **I/O Supply Voltage (quiet)**

Quiet supply voltage to the input buffers of each I/O bank. *x* is the bank number. Within the package, the VMV plane biases the input stage of the I/Os in the I/O banks. This minimizes the noise transfer within the package and improves input signal integrity. Each bank must have at least one VMV connection, and no VMV should be left unconnected. All I/Os in a bank run off the same VMVx supply. VMV is used to provide a quiet supply voltage to the input buffers of each I/O bank. VMVx can be 1.2 V, 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VMV pins tied to GND. VMV and VCCI should be at the same voltage within a given I/O bank. Used VMV pins must be connected to the corresponding VCCI pins of the same bank (i.e., VMV0 to VCCIB0, VMV1 to VCCIB1, etc.).

VCCPLA/B/C/D/E/F **PLL Supply Voltage**

Supply voltage to analog PLL, nominally 1.5 V or 1.2 V.

- 1.5 V for IGLOO V5 devices
- 1.2 V or 1.5 V for IGLOO V2 devices

When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground. Microsemi recommends tying VCCPLx to VCC and using proper filtering circuits to decouple VCC noise from the PLLs. Refer to the PLL Power Supply Decoupling section of the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" chapter of the *IGLOO FPGA Fabric User Guide* for a complete board solution for the PLL analog power supply and ground.

- There is one VCCPLF pin on IGLOO devices.

VCOMPLA/B/C/D/E/F **PLL Ground**

Ground to analog PLL power supplies. When the PLLs are not used, the Microsemi Designer place-and-route tool automatically disables the unused PLLs to lower power consumption. The user should tie unused VCCPLx and VCOMPLx pins to ground.

There is one VCOMPLF pin on IGLOO devices.

VQ100	
Pin Number	**AGL125 Function**
1	GND
2	GAA2/IO67RSB1
3	IO68RSB1
4	GAB2/IO69RSB1
5	IO132RSB1
6	GAC2/IO131RSB1
7	IO130RSB1
8	IO129RSB1
9	GND
10	GFB1/IO124RSB1
11	GFB0/IO123RSB1
12	VCOMPLF
13	GFA0/IO122RSB1
14	VCCPLF
15	GFA1/IO121RSB1
16	GFA2/IO120RSB1
17	VCC
18	VCCIB1
19	GEC0/IO111RSB1
20	GEB1/IO110RSB1
21	GEB0/IO109RSB1
22	GEA1/IO108RSB1
23	GEA0/IO107RSB1
24	VMV1
25	GNDQ
26	GEA2/IO106RSB1
27	FF/GEB2/IO105RSB1
28	GEC2/IO104RSB1
29	IO102RSB1
30	IO100RSB1
31	IO99RSB1
32	IO97RSB1
33	IO96RSB1
34	IO95RSB1
35	IO94RSB1

VQ100	
Pin Number	**AGL125 Function**
36	IO93RSB1
37	VCC
38	GND
39	VCCIB1
40	IO87RSB1
41	IO84RSB1
42	IO81RSB1
43	IO75RSB1
44	GDC2/IO72RSB1
45	GDB2/IO71RSB1
46	GDA2/IO70RSB1
47	TCK
48	TDI
49	TMS
50	VMV1
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO65RSB0
58	GDC0/IO62RSB0
59	GDC1/IO61RSB0
60	GCC2/IO59RSB0
61	GCB2/IO58RSB0
62	GCA0/IO56RSB0
63	GCA1/IO55RSB0
64	GCC0/IO52RSB0
65	GCC1/IO51RSB0
66	VCCIB0
67	GND
68	VCC
69	IO47RSB0
70	GBC2/IO45RSB0
71	GBB2/IO43RSB0

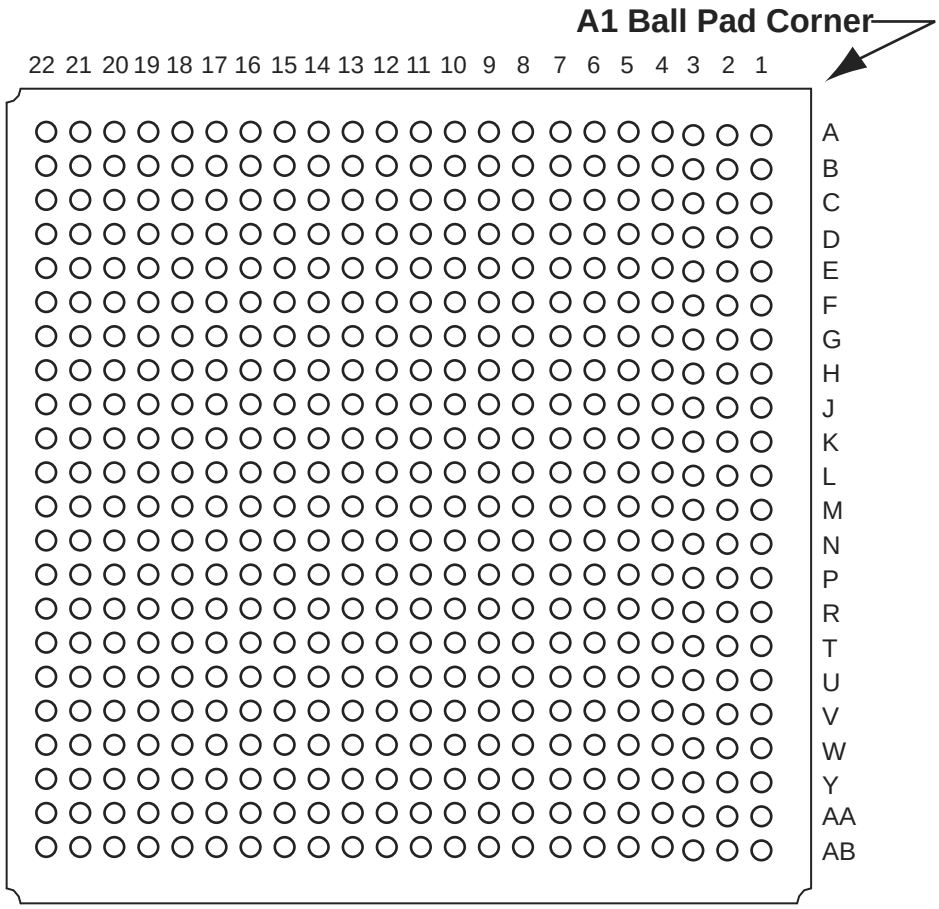
VQ100	
Pin Number	**AGL125 Function**
72	IO42RSB0
73	GBA2/IO41RSB0
74	VMV0
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO32RSB0
83	IO28RSB0
84	IO25RSB0
85	IO22RSB0
86	IO19RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	IO09RSB0
94	IO07RSB0
95	GAC1/IO05RSB0
96	GAC0/IO04RSB0
97	GAB1/IO03RSB0
98	GAB0/IO02RSB0
99	GAA1/IO01RSB0
100	GAA0/IO00RSB0

FG144	
Pin Number	**AGL400 Function**
K1	GEB0/IO136NDB3
K2	GEA1/IO135PDB3
K3	GEA0/IO135NDB3
K4	GEA2/IO134RSB2
K5	IO127RSB2
K6	IO121RSB2
K7	GND
K8	IO104RSB2
K9	GDC2/IO82RSB2
K10	GND
K11	GDA0/IO79VDB1
K12	GDB0/IO78VDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO133RSB2
L4	IO128RSB2
L5	VCCIB2
L6	IO119RSB2
L7	IO114RSB2
L8	IO110RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO132RSB2
M3	IO129RSB2
M4	IO126RSB2
M5	IO124RSB2
M6	IO122RSB2
M7	IO117RSB2
M8	IO115RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	**AGL600 Function**
K1	GEB0/IO145NDB3
K2	GEA1/IO144PDB3
K3	GEA0/IO144NDB3
K4	GEA2/IO143RSB2
K5	IO119RSB2
K6	IO111RSB2
K7	GND
K8	IO94RSB2
K9	GDC2/IO91RSB2
K10	GND
K11	GDA0/IO88NDB1
K12	GDB0/IO87NDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO142RSB2
L4	IO136RSB2
L5	VCCIB2
L6	IO115RSB2
L7	IO103RSB2
L8	IO97RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO141RSB2
M3	IO138RSB2
M4	IO123RSB2
M5	IO126RSB2
M6	IO134RSB2
M7	IO108RSB2
M8	IO99RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG144	
Pin Number	**AGL1000 Function**
K1	GEB0/IO189NDB3
K2	GEA1/IO188PDB3
K3	GEA0/IO188NDB3
K4	GEA2/IO187RSB2
K5	IO169RSB2
K6	IO152RSB2
K7	GND
K8	IO117RSB2
K9	GDC2/IO116RSB2
K10	GND
K11	GDA0/IO113NDB1
K12	GDB0/IO112NDB1
L1	GND
L2	VMV3
L3	FF/GEB2/IO186RSB2
L4	IO172RSB2
L5	VCCIB2
L6	IO153RSB2
L7	IO144RSB2
L8	IO140RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO185RSB2
M3	IO173RSB2
M4	IO168RSB2
M5	IO161RSB2
M6	IO156RSB2
M7	IO145RSB2
M8	IO141RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

FG484



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

FG484	
Pin Number	**AGL400 Function**
C21	NC
C22	VCCIB1
D1	NC
D2	NC
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO17RSB0
D10	IO22RSB0
D11	IO28RSB0
D12	IO34RSB0
D13	IO37RSB0
D14	IO41RSB0
D15	IO43RSB0
D16	GBB1/IO57RSB0
D17	GBA0/IO58RSB0
D18	GBA1/IO59RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	NC
E2	NC
E3	GND
E4	GAB2/IO154UDB3
E5	GAA2/IO155UDB3
E6	IO12RSB0
E7	GAB1/IO03RSB0
E8	IO13RSB0
E9	IO14RSB0
E10	IO21RSB0
E11	IO27RSB0
E12	IO32RSB0

FG484	
Pin Number	**AGL600 Function**
Y7	NC
Y8	VCC
Y9	VCC
Y10	NC
Y11	NC
Y12	NC
Y13	NC
Y14	VCC
Y15	VCC
Y16	NC
Y17	NC
Y18	GND
Y19	NC
Y20	NC
Y21	NC
Y22	VCCIB1

Datasheet Categories

Categories

In order to provide the latest information to designers, some datasheet parameters are published before data has been fully characterized from silicon devices. The data provided for a given device, as highlighted in the "IGLOO Device Status" table, is designated as either "Product Brief," "Advance," "Preliminary," or "Production." The definitions of these categories are as follows:

Product Brief

The product brief is a summarized version of a datasheet (advance or production) and contains general product information. This document gives an overview of specific device and family information.

Advance

This version contains initial estimated information based on simulation, other products, devices, or speed grades. This information can be used as estimates, but not for production. This label only applies to the DC and Switching Characteristics chapter of the datasheet and will only be used when the data has not been fully characterized.

Preliminary

The datasheet contains information based on simulation and/or initial characterization. The information is believed to be correct, but changes are possible.

Unmarked (production)

This version contains information that is considered to be final.

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